

LQ10N200CQ

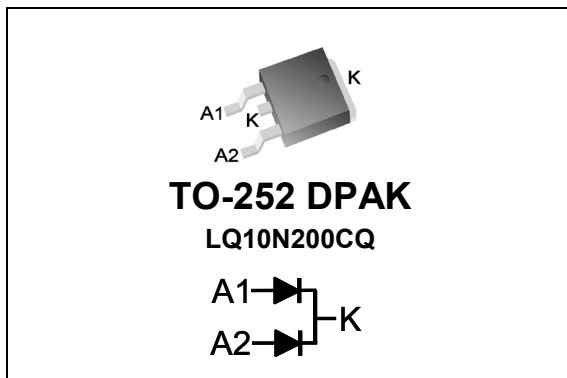
Qspeed™ Automotive Family

200 V, 10 A Common-Cathode Diode for Audio Automotive Applications

Product Summary

$I_{F(AVG)}$ per diode	5	A
V_{RRM}	200	V
Q_{RR} (Typ at 125 °C)	32.4	nC
I_{RRM} (Typ at 125 °C)	2.6	A
Softness t_b/t_a (Typ at 125 °C)	0.39	

Pin Assignment



RoHS Compliant

Package uses Lead-free plating and "Green" mold compound Halogen free per IEC 61249-2-21.

Absolute Maximum Ratings

Absolute maximum ratings are the values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Symbol	Parameter	Conditions	Rating	Units
V_{RRM}	Peak repetitive reverse voltage	$T_J = 25\text{ °C}$	200	V
$I_{F(AVG)}$	Average forward current	Per Diode, $T_J = 150\text{ °C}$, $T_C = 130\text{ °C}$	5	A
		Per Device, $T_J = 150\text{ °C}$, $T_C = 130\text{ °C}$	10	A
I_{FSM}	Non-repetitive peak surge current	Per Diode, 60 Hz, 1/2 cycle	60	A
I_{FSM}	Non-repetitive peak surge current	Per Diode, 1/2 cycle of $t = 28\text{ }\mu\text{s}$ Sinusoid, $T_C = 25\text{ °C}$	350	A
T_J	Operating junction temperature range		-40 to 150	°C
T_{STG}	Storage temperature		-55 to 150	°C
	Lead soldering temperature	Leads at 1.6mm from case, 10 sec	300	°C
P_D	Power dissipation	$T_C = 25\text{ °C}$	27.7	W

Thermal Resistance

Symbol	Resistance from:	Conditions	Rating	Units
$R_{\theta JC}$	Junction to case	Per Diode	4.5	°C/W
		Per Device	2.3	°C/W

General Description

This device has the lowest Q_{RR} of any 200 V Silicon diode. Its recovery characteristics increase efficiency, reduce EMI and eliminate snubbers.

Applications

- Automotive
 - AEC-Q101 qualified
 - Fab, assembly and test certified to IATF 16949
 - ESD HBM classification H0

Features

- Low Q_{RR} , Low I_{RRM} , Low t_{RR}
- Soft recovery

Benefits

- Increases efficiency
 - Eliminates need for snubber circuits
 - Reduces EMI filter component size and count
- Enables extremely fast switching

Electrical Specifications at $T_J = 25\text{ }^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
DC Characteristics per diode							
I_R	Reverse current per diode	$V_R = 200\text{ V}, T_J = 25\text{ }^\circ\text{C}$	-	-	250	μA	
		$V_R = 200\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	0.23	-	mA	
V_F	Forward voltage per diode	$I_F = 5\text{ A}, T_J = 25\text{ }^\circ\text{C}$	-	0.95	1.1	V	
		$I_F = 5\text{ A}, T_J = 150\text{ }^\circ\text{C}$	-	0.8	-	V	
C_J	Junction capacitance per diode	$V_R = 10\text{ V}, 1\text{ MHz}$	-	22	-	pF	
Dynamic Characteristics per diode							
t_{RR}	Reverse recovery time, per diode	$dI_F/dt = 200\text{ A}/\mu\text{s}$ $V_R = 130\text{ V},$ $I_F = 5\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$	-	13.9	-	ns
			$T_J = 125\text{ }^\circ\text{C}$	-	19.5	-	ns
Q_{RR}	Reverse recovery charge, per diode	$dI_F/dt = 200\text{ A}/\mu\text{s}$ $V_R = 130\text{ V},$ $I_F = 5\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$	-	15.6	25.5	nC
			$T_J = 125\text{ }^\circ\text{C}$	-	32.4	-	nC
I_{RRM}	Maximum reverse recovery current, per diode	$dI_F/dt = 200\text{ A}/\mu\text{s}$ $V_R = 130\text{ V},$ $I_F = 5\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$	-	1.78	2.65	A
			$T_J = 125\text{ }^\circ\text{C}$	-	2.6	-	A
S	Softness per diode = $\frac{t_b}{t_a}$	$dI_F/dt = 200\text{ A}/\mu\text{s}$ $V_R = 130\text{ V},$ $I_F = 5\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$	-	0.44	-	
			$T_J = 125\text{ }^\circ\text{C}$	-	0.39	-	

Note to component engineers: Q-Series diodes employ Schottky technologies in their design and construction. Therefore, component engineers should plan their test setups to be similar to traditional Schottky test setups. (For further details, see application note AN-300.)

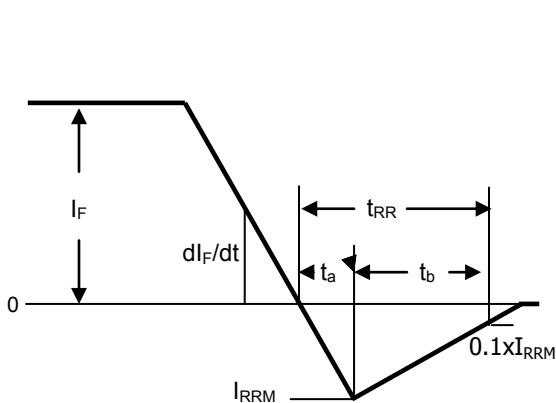


Figure 1. Reverse Recovery Definitions

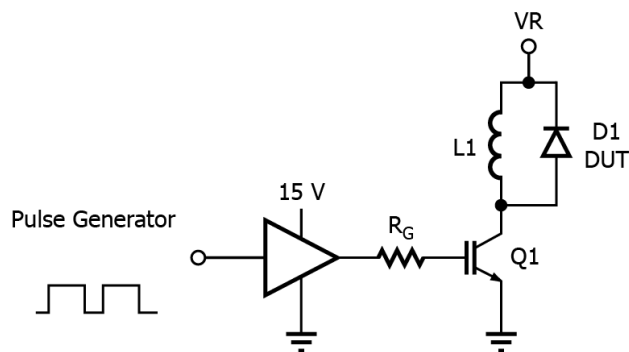


Figure 2. Reverse Recovery Test Circuit

PI-7614-041315

Electrical Specifications at $T_J = 25\text{ }^\circ\text{C}$ (unless otherwise specified)

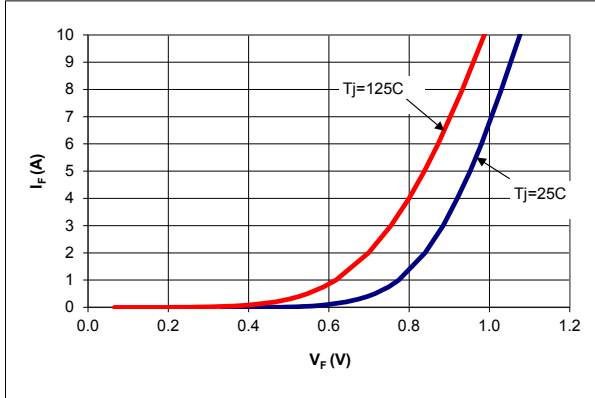


Figure 3. Typical I_F vs. V_F

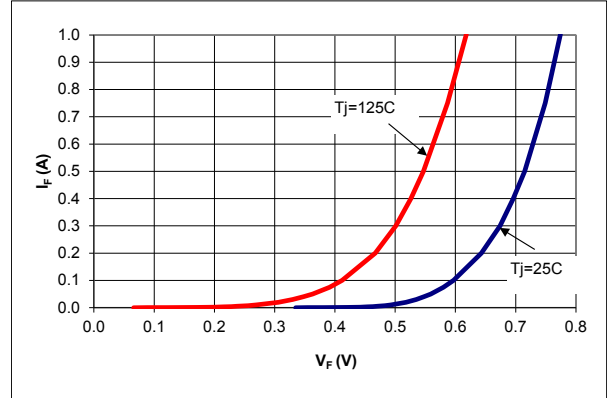


Figure 4. Typical I_F vs. V_F

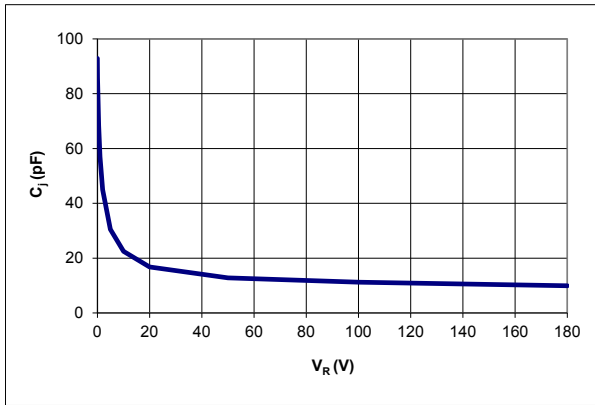


Figure 5. Typical C_J vs. V_R

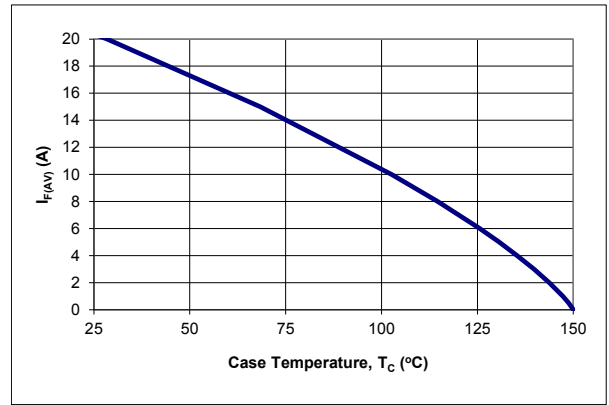


Figure 6. DC Current Derating Curve

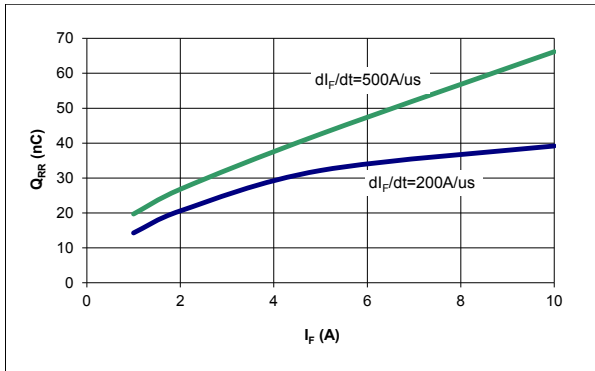


Figure 7. Typical Q_{RR} vs. I_F at $T_J=125\text{ }^\circ\text{C}$

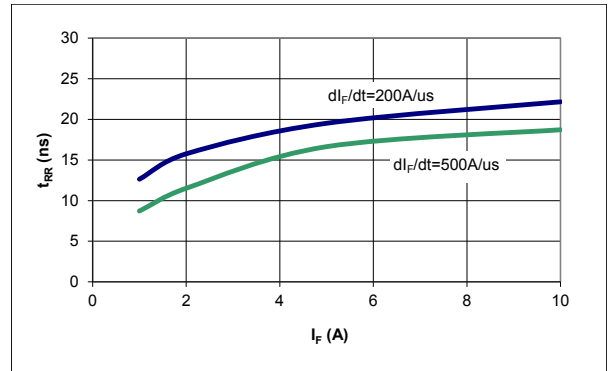


Figure 8. Typical t_{RR} vs. I_F at $T_J=125\text{ }^\circ\text{C}$

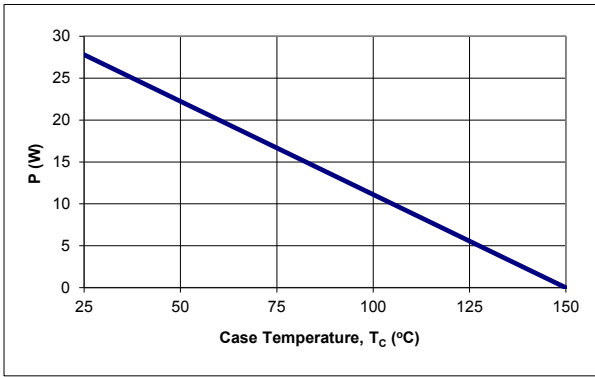


Figure 9. Power Derating Curve

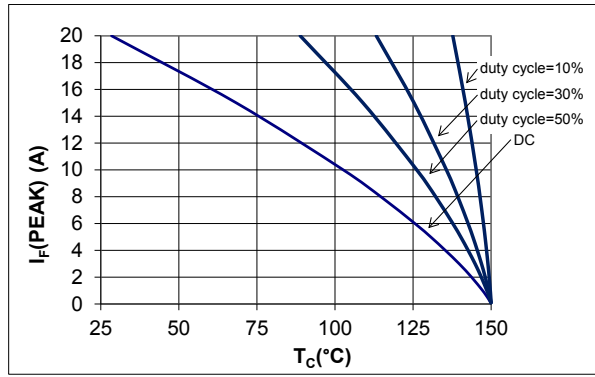


Figure 10. I_f (Peak) vs. TC, $f = 70$ kHz

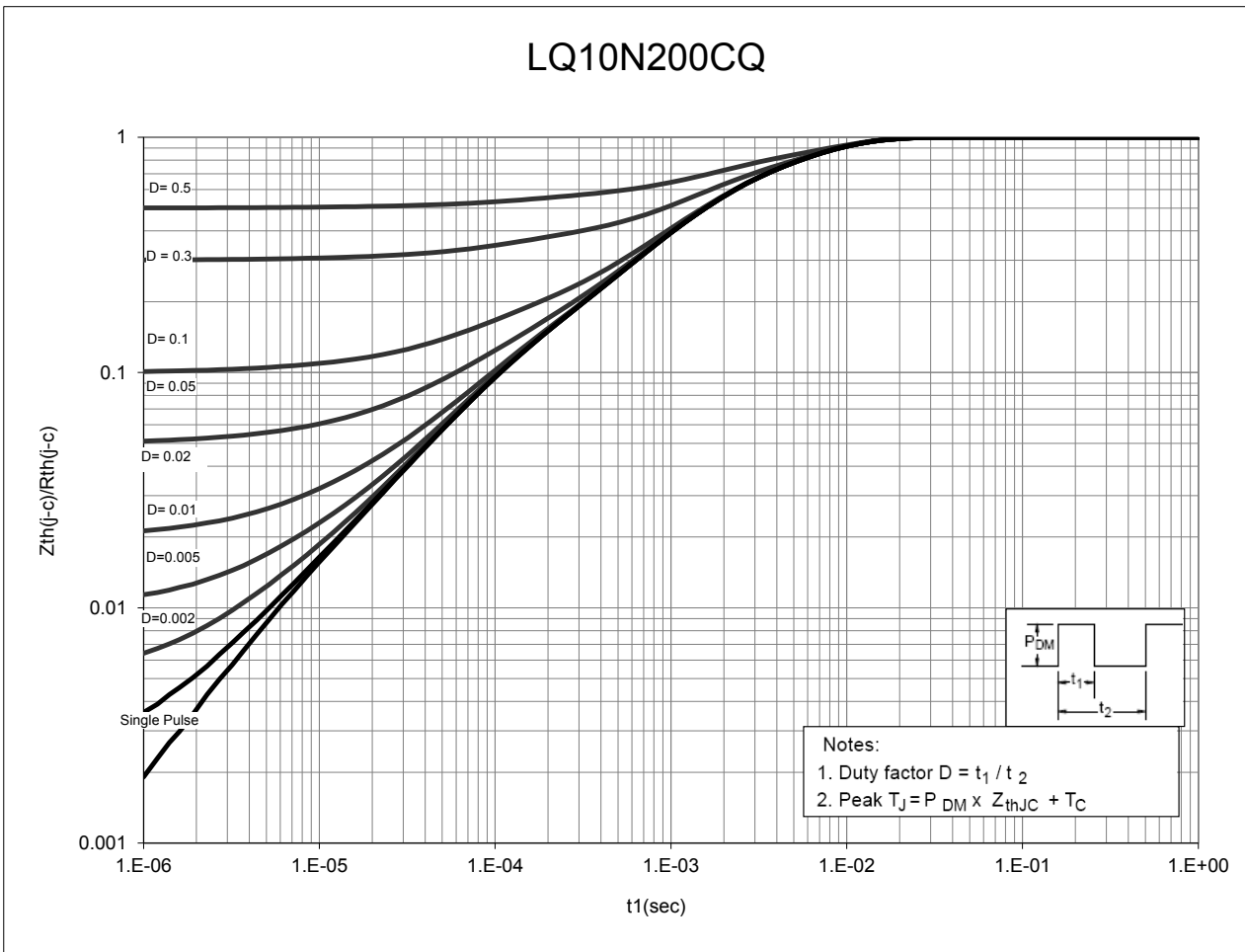
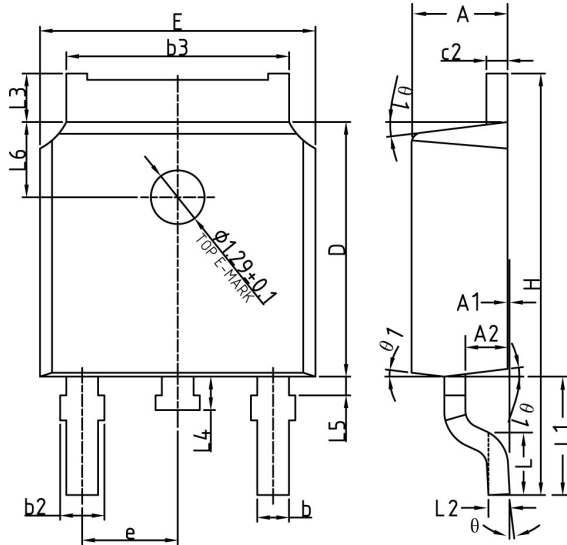


Figure 11. Normalized Maximum Transient Thermal Impedance

Dimensional Outline Drawings

TO-252 DPAK



Dim	Millimeters	
	MIN	MAX
A	2.20	2.38
A1	0	0.10
A2	0.90	1.10
b	0.72	0.85
b2	0.72	0.90
b3	5.13	5.46
c2	0.47	0.60
D	6.00	6.20
E	6.50	6.70
e	2.186	2.386
H	9.80	10.40
L	1.40	1.70
L1	2.90 REF	
L2	0.51 BSC	
L3	0.90	1.25
L4	0.60	1.00
L5	0.15	0.75
L6	1.80 REF	
θ	0°	8°
$\theta 1$	5°	9°

Soldering time and temperature: This product has been designed for use with high-temperature, lead-free solder. The component leads can be subjected to a maximum temperature of 300 °C, for up to 10 seconds. See Application Note AN-303, for more details.

Ordering Information

Part Number	Package	Packing
LQ10N200CQ	TO-252 DPAK	2500 units/reel

The information contained in this document is subject to change without notice.

Revision	Notes	Date
1.1	Code A release.	03/19

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Power Integrations Worldwide Sales Support Locations**WORLD HEADQUARTERS**

5245 Hellyer Avenue
San Jose, CA 95138, USA.
Main: +1-408-414-9200
Customer Service:
Worldwide: +1-65-635-64480
Americas: +1-408-414-9621
e-mail: usasales@power.com

CHINA (SHANGHAI)

Rm 2410, Charity Plaza, No. 88,
North Caoxi Road,
Shanghai, PRC 200030
Phone: +86-21-6354-6323
e-mail: chinasales@power.com

CHINA (SHENZHEN)

17/F, Hivac Building, No. 2, Keji
Nan 8th Road, Nanshan District,
Shenzhen, China, 518057
Phone: +86-755-8672-8689
e-mail: chinasales@power.com

GERMANY (AC-DC/LED Sales)

Einsteinring 24
85609 Dornach/Aschheim
Germany
Tel: +49-89-5527-39100
e-mail: eurosales@power.com

GERMANY (Gate Driver Sales)

HellwegForum 1
59469 Ense
Germany
Tel: +49-2938-64-39990
e-mail: igbt-driver.sales@power.com

INDIA

#1, 14th Main Road
Vasanthanagar
Bangalore-560052
India
Phone: +91-80-4113-8020
e-mail: indiasales@power.com

ITALY

Via Milanese 20, 3rd. Fl.
20099 Sesto San Giovanni (MI) Italy
Phone: +39-024-550-8701
e-mail: eurosales@power.com

JAPAN

Yusen Shin-Yokohama 1-chome Bldg.
1-7-9, Shin-Yokohama, Kohoku-ku
Yokohama-shi,
Kanagawa 222-0033 Japan
Phone: +81-45-471-1021
e-mail: japansales@power.com

KOREA

RM 602, 6FL
Korea City Air Terminal B/D,
159-6
Samsung-Dong, Kangnam-Gu,
Seoul, 135-728 Korea
Phone: +82-2-2016-6610
e-mail: koreasales@power.com

SINGAPORE

51 Newton Road,
#19-01/05 Goldhill Plaza
Singapore, 308900
Phone: +65-6358-2160
e-mail: singaporesales@power.com

TAIWAN

5F, No. 318, Nei Hu Rd.,
Sec. 1
Nei Hu District
Taipei 11493, Taiwan R.O.C.
Phone: +886-2-2659-4570
e-mail: taiwansales@power.com

UK

Building 5, Suite 21
The Westbrook Centre
Milton Road
Cambridge
CB4 1YG
Phone: +44 (0) 7823-557484
e-mail: eurosales@power.com